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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	56800EX
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	CANbus, I²C, LINbus, SCI, SPI
Peripherals	Brown-out Detect/Reset, DMA, LVD, POR, PWM, WDT
Number of I/O	68
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 3.6V
Data Converters	A/D 16x12b, 10x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-FQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc56f84786vlk

1 Overview

1.1 MC56F844x/5x/7x Product Family

The following table highlights major features, including features that differ among members of the family. Features not listed are shared by all members of the family.

Table 1. 56F844x/5x/7x Family

Part Number	MC56F84																	
	789	**786**	**769**	**766**	**763**	**553**	**550**	**543**	**540**	**587**	**585**	**567**	**565**	**462**	**452**	**451**	**442**	**441**
Core freq. (MHz)	100	100	100	100	100	80	80	80	80	80	80	80	80	60	60	60	60	60
Flash memory (KB)	256	256	128	128	128	96	96	64	64	256	256	128	128	128	96	96	64	64
FlevNVM/ FlexRAM (KB)	32/2	32/2	32/2	32/2	32/2	32/2	32/2	32/2	32/2	32/2	32/2	32/2	32/2	32/2	32/2	32/2	32/2	32/2
Total flash memory (KB)[1]	288	288	160	160	160	128	128	96	96	288	288	160	160	160	128	128	96	96
RAM (KB)	32	32	24	24	24	16	16	8	8	32	32	24	24	24	16	16	8	8
Memory resource protection	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes	Yes
External Watchdog	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1
12-bit Cyclic ADC channels	2x8 (300 ns)	2x8 (300 ns)	2x8 (300 ns)	2x8 (300 ns)	2x8 (300 ns)	2x8 (300 ns)	2x5 (300 ns)	2x8 (300 ns)	2x5 (300 ns)	2x8 (600 ns)	2x8 (600 ns)	2x8 (600 ns)	2x8 (600 ns)	2x8 (600 ns)	2x8 (600 ns)	2x5 (600 ns)	2x8 (600 ns)	2x5 (600 ns)
16-bit SAR ADC (with Temp Sensor) channels	1x 16	1x 10	1x 16	1x 10	1x8	1x8	0	1x8	0	1x 16	1x 10	1x 16	1x 10	0	1x8	0	1x8	0
PWMA with input capture:																		
High-resolution channels	1x8	1x8	1x8	1x8	1x8	1x8	1x6	1x8	1x6	0	0	0	0	0	0	0	0	0
Standard channels	4	1	4	1	1	1	0	1	0	2x 12	1x 12, 1x9	2x 12	1x 12, 1x9	1x9	1x9	1x6	1x9	1x6

Table continues on the next page...

- Parallel instruction set with unique DSP addressing modes
- Hardware DO and REP loops
- Bit reverse address mode, effectively supporting DSP and Fast Fourier Transform algorithms
- Full shadowing of the register stack for zero-overhead context saves and restores: nine shadow registers corresponding to the R0, R1, R2, R3, R4, R5, N, N3, and M01 address registers
- Instruction set supporting both DSP and controller functions
- Controller-style addressing modes and instructions for compact code
- Enhanced bit manipulation instruction set
- Efficient C compiler and local variable support
- Software subroutine and interrupt stack with depth limited only by memory
- Priority level setting for interrupt levels
- JTAG/Enhanced On-Chip Emulation (OnCE) for unobtrusive, real-time debugging that is independent of processor speed

1.3 Operation Parameters

- Up to 100 MHz operation at -40 °C to 105 °C ambient temperature
- Single 3.3 V power supply
- Supply range: V_{DD} - V_{SS} = 2.7 V to 3.6 V, V_{DDA} - V_{SSA} = 2.7 V to 3.6 V

1.4 On-Chip Memory and Memory Protection

- Modified dual Harvard architecture permits as many as three simultaneous accesses to program and data memory
- Internal flash memory with security and protection to prevent unauthorized access
- Memory resource protection (MRP) unit to protect supervisor programs and resources from user programs
- Programming code can reside in flash memory during flash programming
- The dual-ported RAM controller supports concurrent instruction fetches and data accesses, or dual data accesses, by the DSC core.
  - Concurrent accesses provide increased performance.
  - The data and instruction arrive at the core in the same cycle, reducing latency.
- On-chip memory
  - Up to 144 KW program/data flash memory, including FlexNVM
  - Up to 16 KW dual port data/program RAM

- PWM outputs can be configured as complementary output pairs or independent outputs
- Dedicated time-base counter with period and frequency control per submodule
- Independent top and bottom deadtime insertion for each complementary pair
- Independent control of both edges of each PWM output
- Enhanced input capture and output compare functionality on each input
  - Channels not used for PWM generation can be used for buffered output compare functions
  - Channels not used for PWM generation can be used for input capture functions
  - Enhanced dual edge capture functionality
- Synchronization of submodule to external hardware or other PWM supported
- Double buffered PWM registers
  - Integral reload rates from 1 to 16
  - Half-cycle reload capability
- Multiple output trigger events can be generated per PWM cycle via hardware
- Support for double switching PWM outputs
- Up to eight fault inputs can be assigned to control multiple PWM outputs
  - Programmable filters for fault inputs
- Independently programmable PWM output polarity
- Individual software control of each PWM output
- All outputs can be programmed to change simultaneously via a FORCE_OUT event
- PWMX pin can optionally output a third PWM signal from each submodule
- Option to supply the source for each complementary PWM signal pair from any of the following:
  - Crossbar module outputs
  - External ADC input, taking into account values set in ADC high and low limit registers

1.6.2 12-bit Analog-to-Digital Converter (Cyclic type)

- Two independent 12-bit analog-to-digital converters (ADCs)
  - 2 x 8-channel external inputs
  - Built-in x1, x2, x4 programmable gain pre-amplifier
  - Maximum ADC clock frequency is up to 20 MHz with as low as 50 ns period
  - Single conversion time of 8.5 ADC clock cycles
  - Additional conversion time of 6 ADC clock cycles
- Support of analog inputs for single-ended and differential conversions
- Sequential, parallel, and independent scan mode
- First 8 samples have offset, limit and zero-crossing calculation supported
- ADC conversions can be synchronized by any module connected to internal crossbar module, such as PWM and timer modules and GPIO and comparators

1.6.6 Quad Timer

- Four 16-bit up/down counters with programmable prescaler for each counter
- Operation modes: edge count, gated count, signed count, capture, compare, PWM, signal shot, single pulse, pulse string, cascaded, quadrature decode
- Programmable input filter
- Counting start can be synchronized across counters

1.6.7 Queued Serial Communications Interface (QSCI) Modules

- Operating clock up to two times CPU operating frequency
- Four-word-deep FIFOs available on both transmit and receive buffers
- Standard mark/space non-return-to-zero (NRZ) format
- 13-bit integer and 3-bit fractional baud rate selection
- Full-duplex or single-wire operation
- Programmable 8-bit or 9-bit data format
- Error detection capability
- Two receiver wakeup methods:
  - Idle line
  - Address mark
- 1/16 bit-time noise detection

1.6.8 Queued Serial Peripheral Interface (QSPI) Modules

- Maximum 25 Mbps baud rate
- Selectable baud rate clock sources for low baud rate communication
- Baud rate as low as Baudrate_Freq_in / 8192
- Full-duplex operation
- Master and slave modes
- Double-buffered operation with separate transmit and receive registers
- Four-word-deep FIFOs available on transmit and receive buffers
- Programmable length transmissions (2 bits to 16 bits)
- Programmable transmit and receive shift order (MSB as first bit transmitted)

1.6.9 Inter-Integrated Circuit (I2C)/System Management Bus (SMBus) Modules

- Compatible with I2C bus standard
- Support for System Management Bus (SMBus) specification, version 2
- Multi-master operation

1.6.12 Power Supervisor

- Power-on reset (POR) to reset CPU, peripherals, and JTAG/EOnCE controllers (VDD > 2.1 V)
- Brownout reset (VDD < 1.9 V)
- Critical warn low voltage interrupt (LVI2.0)
- Peripheral low voltage interrupt (LVI2.7)

1.6.13 Phase Locked Loop

- Wide programmable output frequency: 240 MHz to 400 MHz
- Input reference clock frequency: 8 MHz to 16 MHz
- Detection of loss of lock and loss of reference clock
- Ability to power down

1.6.14 Clock sources

1.6.14.1 On-Chip Oscillators

- Tunable 8 MHz relaxation oscillator with 400 kHz at standby mode (divide-by-two output)
- 32 kHz low frequency clock as secondary clock source for COP, EWM, PIT

1.6.14.2 Crystal Oscillator

- Support for both high ESR crystal oscillator (greater than 100-ohm ESR) and ceramic resonator
- 4 MHz to 16 MHz operating frequency

1.6.15 Cyclic Redundancy Check (CRC) Generator

- Hardware 16/32-bit CRC generator
- High-speed hardware CRC calculation
- Programmable initial seed value
- Programmable 16/32-bit polynomial
- Error detection for all single, double, odd, and most multi-bit errors

- Option to transpose input data or output data (CRC result) bitwise or bytewise,[1] which is required for certain CRC standards
- Option for inversion of final CRC result

1.6.16 General Purpose I/O (GPIO)

- 5 V tolerance
- Individual control of peripheral mode or GPIO mode for each pin
- Programmable push-pull or open drain output
- Configurable pullup or pulldown on all input pins
- All pins except JTAG and RESETB pins default to be GPIO inputs
- 2 mA / 9 mA source/sink capability
- Controllable output slew rate

1.7 Block Diagrams

The 56800EX core is based on a modified dual Harvard-style architecture consisting of three execution units operating in parallel, allowing as many as six operations per instruction cycle. The MCU-style programming model and optimized instruction set allow straightforward generation of efficient, compact DSP and control code. The instruction set is also highly efficient for C compilers to enable rapid development of optimized control applications.

The device's basic architecture appears in Figure 1 and Figure 2. Figure 1 illustrates how the 56800EX system buses communicate with internal memories and the IPBus interface and the internal connections among each unit of the 56800EX core. Figure 2 shows the peripherals and control blocks connected to the IPBus bridge. See the specific device’s Reference Manual for details.

1. A bytewise transposition is not possible when accessing the CRC data register via 8-bit accesses. In this case, user software must perform the bytewise transposition.

4.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

4.2 Format

Part numbers for this device have the following format: Q 56F8 4 C F P T PP N

4.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	• MC = Fully qualified, general market flow • PC = Prequalification
56F8	DSC family with flash memory and DSP56800/ DSP56800E/DSP56800EX core	• 56F8
4	DSC subfamily	• 4
C	Maximum CPU frequency (MHz)	• 4 = 60 MHz • 5 = 80 MHz • 7 = 100 MHz
F	Primary program flash memory size	• 4 = 64 KB • 5 = 96 KB • 6 = 128 KB • 8 = 256 KB
P	Pin count	• 0 and 1 = 48 • 2 and 3 = 64 • 4, 5, and 6 = 80 • 7, 8, and 9 = 100
T	Temperature range (°C)	• V = –40 to 105
PP	Package identifier	• LF = 48LQFP • LH = 64LQFP • LK = 80LQFP • LL = 100LQFP
N	Packaging type	• R = Tape and reel • (Blank) = Trays

4.4 Example

This is an example part number: MC56F84789VLL

5 Terminology and guidelines

5.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

5.1.1 Example

This is an example of an operating requirement, which you must meet for the accompanying operating behaviors to be guaranteed:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	0.9	1.1	V

5.2 Definition: Operating behavior

An *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

5.2.1 Example

This is an example of an operating behavior, which is guaranteed if you meet the accompanying operating requirements:

Symbol	Description	Min.	Max.	Unit
I_{WP}	Digital I/O weak pullup/ pulldown current	10	130	µA

5.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

5.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

5.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

5.4.1 Example

This is an example of an operating rating:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	–0.3	1.2	V

5.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	°C
V_{DD}	3.3 V supply voltage	3.3	V

6 Ratings

6.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

6.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

6.3 ESD handling ratings

Although damage from electrostatic discharge (ESD) is much less common on these devices than on early CMOS circuits, use normal handling precautions to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with AEC-Q100 Stress Test Qualification. During the device qualification ESD stresses were performed for the human body model (HBM), the machine model (MM), and the charge device model (CDM).

All latch-up testing is in conformity with AEC-Q100 Stress Test Qualification.

A device is defined as a failure if after exposure to ESD pulses the device no longer meets the device specification. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

Table 3. ESD/Latch-up Protection

Characteristic[1]	Min	Max	Unit
ESD for Human Body Model (HBM)	–2000	+2000	V
ESD for Machine Model (MM)	–200	+200	V
ESD for Charge Device Model (CDM)	–500	+500	V
Latch-up current at TA= 85°C (I_{LAT})	–100	+100	mA

1. Parameter is achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted.

6.4 Voltage and current operating ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 4 may affect device reliability or cause permanent damage to the device.

Table 4. Absolute Maximum Ratings (V_{SS} = 0 V, V_{SSA} = 0 V)

Characteristic	Symbol	Notes[1]	Min	Max	Unit
Supply Voltage Range	V_{DD}		-0.3	4.0	V
Analog Supply Voltage Range	V_{DDA}		-0.3	4.0	V
ADC High Voltage Reference	V_{REFHx}		-0.3	4.0	V
Voltage difference V_{DD} to V_{DDA}	ΔV_{DD}		-0.3	0.3	V
Voltage difference V_{SS} to V_{SSA}	ΔV_{SS}		-0.3	0.3	V

Table continues on the next page...

- Pin Group 3: ADC and Comparator Analog Inputs
- Pin Group 4: XTAL, EXTAL
- Pin Group 5: DAC analog output

2. ADC (Cyclic) specifications are not guaranteed when V_{DDA} is below 3.0 V.
3. Total chip source or sink current cannot exceed 75 mA.
4. Contiguous pin DC injection current of regional limit—includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins—is 25 mA.

7.3.2 LVD and POR operating requirements

Table 6. PMC Low-Voltage Detection (LVD) and Power-On Reset (POR) Parameters

Characteristic	Symbol	Min	Typ	Max	Unit
POR Assert Voltage[1]	POR		2.0		V
POR Release Voltage[2]	POR		2.7		V
LVI_2p7 Threshold Voltage			2.73		V
LVI_2p2 Threshold Voltage			2.23		V

1. During 3.3-volt V_{DD} power supply ramp down
2. During 3.3-volt V_{DD} power supply ramp up (gated by LVI_2p7)

7.3.3 Voltage and current operating behaviors

The following table provides information about power supply requirements and I/O pin characteristics.

Table 7. DC Electrical Characteristics at Recommended Operating Conditions

Characteristic	Symbol	Notes[1]	Min	Typ	Max	Unit	Test Conditions
Output Voltage High	V_{OH}	Pin Group 1	V_{DD} - 0.5	—	—	V	$I_{OH} = I_{OHmax}$
Output Voltage Low	V_{OL}	Pin Groups 1, 2	—	—	0.5	V	$I_{OL} = I_{OLmax}$
Digital Input Current High	I_{IH}	Pin Group 1	—	0	+/- 2.5	µA	V_{IN} = 2.4 V to 5.5 V
pull-up enabled or disabled		Pin Group 2					V_{IN} = 2.4 V to V_{DD}
Comparator Input Current High	I_{IHC}	Pin Group 3	—	0	+/- 2	µA	$V_{IN} = V_{DDA}$
Oscillator Input Current High	I_{IHOSC}	Pin Group 3	—	0	+/- 2	µA	$V_{IN} = V_{DDA}$
Internal Pull-Up Resistance	$R_{Pull-Up}$		20	—	50	kΩ	—
Internal Pull-Down Resistance	$R_{Pull-Down}$		20	—	50	kΩ	—

Table continues on the next page...

8.3.4 Relaxation Oscillator Timing

Table 20. Relaxation Oscillator Electrical Specifications

Characteristic	Symbol	Min	Typ	Max	Unit
8 MHz Output Frequency[1] RUN Mode • 0°C to 105°C • -40°C to 105°C Standby Mode (IRC trimmed @ 8 MHz) • -40°C to 105°C		 7.84 7.76 266.8	 8 8 402	 8.16 8.24 554.3	 MHz kHz
8 MHz Frequency Variation RUN Mode Due to temperature • 0°C to 105°C • -40°C to 105°C			 +/- 1.5 +/- 1.5	 +/-2 +/-3	 %
32 kHz Output Frequency[2] RUN Mode • -40°C to 105°C		 30.1	 32	 33.9	 kHz
32 kHz Output Frequency Variation RUN Mode Due to temperature • -40°C to 105°C			 +/-2.5	 +/-4	 %
Stabilization Time • 8 MHz output[3] • 32 kHz output[4]	tstab		 0.12 14.4	 0.4 16.2	 µs
Output Duty Cycle		48	50	52	%

1. Frequency after application of 8 MHz trim
2. Frequency after application of 32 kHz trim
3. Standby to run mode transition
4. Power down to run mode transition

Table 22. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	Set FlexRAM Function execution time:					
$t_{setramff}$	• Control Code 0xFF	—	50	—	µs	
$t_{setram8k}$	• 8 KB EEPROM backup	—	0.3	0.5	ms	
$t_{setram32k}$	• 32 KB EEPROM backup	—	0.7	1.0	ms	
	Byte-write to FlexRAM for EEPROM operation					
$t_{eewr8bers}$	Byte-write to erased FlexRAM location execution time	—	175	260	µs	3
	Byte-write to FlexRAM execution time:					
$t_{eewr8b8k}$	• 8 KB EEPROM backup	—	340	1700	µs	
$t_{eewr8b16k}$	• 16 KB EEPROM backup	—	385	1800	µs	
$t_{eewr8b32k}$	• 32 KB EEPROM backup	—	475	2000	µs	
	Word-write to FlexRAM for EEPROM operation					
$t_{eewr16bers}$	Word-write to erased FlexRAM location execution time	—	175	260	µs	
	Word-write to FlexRAM execution time:					
$t_{eewr16b8k}$	• 8 KB EEPROM backup	—	340	1700	µs	
$t_{eewr16b16k}$	• 16 KB EEPROM backup	—	385	1800	µs	
$t_{eewr16b32k}$	• 32 KB EEPROM backup	—	475	2000	µs	
	Longword-write to FlexRAM for EEPROM operation					
$t_{eewr32bers}$	Longword-write to erased FlexRAM location execution time	—	360	540	µs	
	Longword-write to FlexRAM execution time:					
$t_{eewr32b8k}$	• 8 KB EEPROM backup	—	545	1950	µs	
$t_{eewr32b16k}$	• 16 KB EEPROM backup	—	630	2050	µs	
$t_{eewr32b32k}$	• 32 KB EEPROM backup	—	810	2250	µs	

1. Assumes 25MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

8.4.1.3 Flash high voltage current behaviors

Table 23. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

8.4.1.4 Reliability specifications

Table 24. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
Program Flash						
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2
Data Flash						
$t_{nvmretd10k}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{nvmretd1k}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{nvmcycd}$	Cycling endurance	10 K	50 K	—	cycles	2
FlexRAM as EEPROM						
$t_{nvmretee100}$	Data retention up to 100% of write endurance	5	50	—	years	
$t_{nvmretee10}$	Data retention up to 10% of write endurance	20	100	—	years	
	Write endurance					3
$n_{nvmwree16}$	• EEPROM backup to FlexRAM ratio = 16	35 K	175 K	—	writes	
$n_{nvmwree128}$	• EEPROM backup to FlexRAM ratio = 128	315 K	1.6 M	—	writes	
$n_{nvmwree512}$	• EEPROM backup to FlexRAM ratio = 512	1.27 M	6.4 M	—	writes	
$n_{nvmwree4k}$	• EEPROM backup to FlexRAM ratio = 4096	10 M	50 M	—	writes	
$n_{nvmwree8k}$	• EEPROM backup to FlexRAM ratio = 8192	20 M	100 M	—	writes	

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at -40°C ≤ T_j ≤ 125°C.
3. Write endurance represents the number of writes to each FlexRAM location at -40°C ≤Tj ≤ 125°C influenced by the cycling endurance of the FlexNVM (same value as data flash) and the allocated EEPROM backup. Minimum and typical values assume all byte-writes to FlexRAM.

8.5 Analog

8.5.1 12-bit Cyclic Analog-to-Digital Converter (ADC) Parameters

Table 25. 12-bit ADC Electrical Specifications

Characteristic	Symbol	Min	Typ	Max	Unit
Recommended Operating Conditions					
Supply Voltage[1]	V_{DDA}	2.7	3.3	3.6	V
Vrefh Supply Voltage[2]	Vrefhx	3.0		V_{DDA}	V
ADC Conversion Clock[3]	f_{ADCCLK}	0.6		20	MHz
Conversion Range	R_{AD}	V_{REFL}		V_{REFH}	V

Table continues on the next page...

7. Input data is 1 kHz sine wave. ADC conversion clock <12MHz.
8. System Clock = 4 MHz, ADC Clock = 2 MHz, AVG = Max, Long Sampling = Max

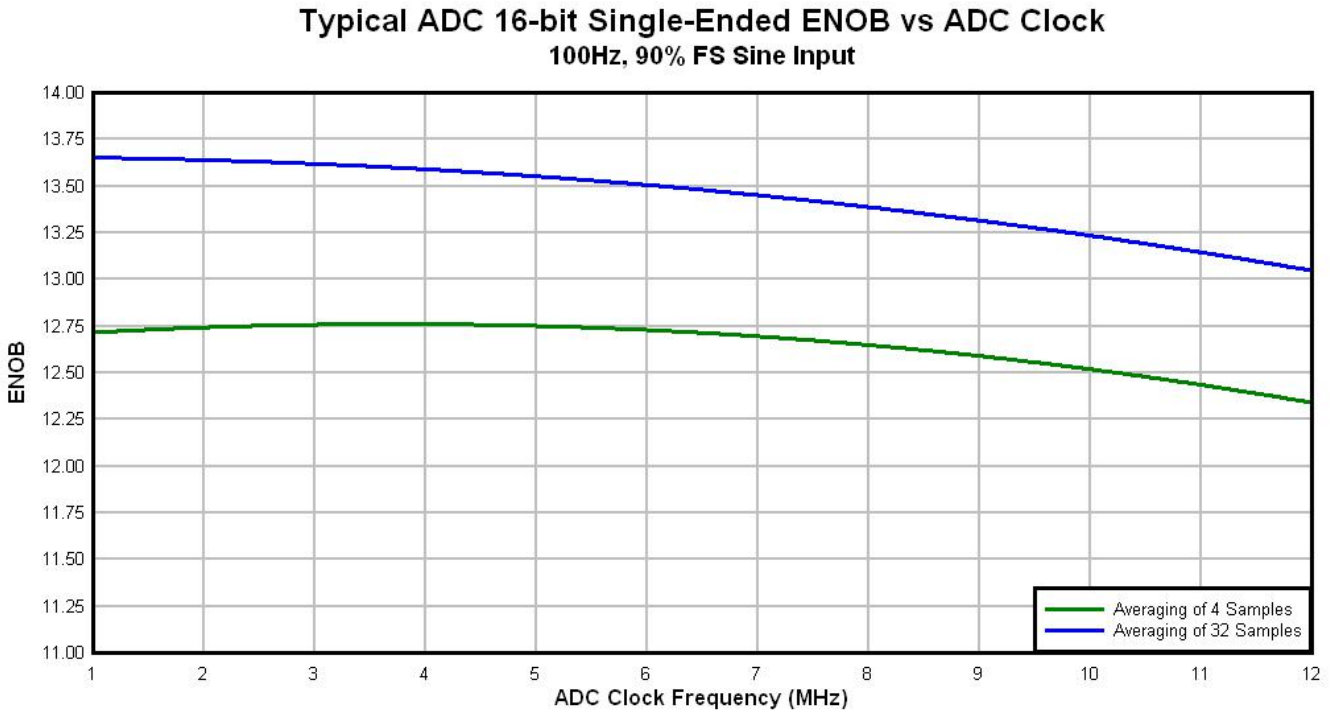

Figure 11. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

8.5.3 12-bit Digital-to-Analog Converter (DAC) Parameters

Table 28. DAC Parameters

Parameter	Conditions/Comments	Symbol	Min	Typ	Max	Unit
DC Specifications						
Resolution			12	12	12	bits
Settling time[1]	At output load RLD = 3 kΩ CLD = 400 pf		—	1		µs
Power-up time	Time from release of PWRDWN signal until DACOUT signal is valid	t_{DAPU}	—	—	11	µs
Accuracy						
Integral non-linearity[2]	Range of input digital words: 410 to 3891 ($19A - $F33) 5% to 95% of full range	INL	—	+/- 3	+/- 4	LSB[3]
Differential non-linearity[2]	Range of input digital words: 410 to 3891 ($19A - $F33) 5% to 95% of full range	DNL	—	+/- 0.8	+/- 0.9	LSB[3]

Table continues on the next page...

The junction-to-ambient thermal resistance is an industry-standard value that provides a quick and easy estimation of thermal performance. Unfortunately, there are two values in common usage: the value determined on a single-layer board and the value obtained on a board with two planes. For packages such as the PBGA, these values can be different by a factor of two. Which value is closer to the application depends on the power dissipated by other components on the board. The value obtained on a single layer board is appropriate for the tightly packed printed circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low-power dissipation and the components are well separated.

When a heat sink is used, the thermal resistance is expressed as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

$$R_{\Theta JA} = R_{\Theta JC} + R_{\Theta CA}$$

Where,

$R_{\Theta JA}$ = Package junction-to-ambient thermal resistance (°C/W)

$R_{\Theta JC}$ = Package junction-to-case thermal resistance (°C/W)

$R_{\Theta CA}$ = Package case-to-ambient thermal resistance (°C/W)

$R_{\Theta JC}$ is device related and cannot be adjusted. You control the thermal environment to change the case to ambient thermal resistance, $R_{\Theta CA}$. For instance, you can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed circuit board, or change the thermal dissipation on the printed circuit board surrounding the device.

To determine the junction temperature of the device in the application when heat sinks are not used, the thermal characterization parameter (YJT) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

Where,

T_T = Thermocouple temperature on top of package (°C/W)

Ψ_{JT} = hermal characterization parameter (°C/W)

P_D = Power dissipation in package (W)

The thermal characterization parameter is measured per JESD51–2 specification using a 40-gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over

100 LQFP	80 LQFP	64 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3
25	20	16	GPIOA3	GPIOA3	ANA3&VREFLA&CMPA_IN2			
26	21	17	GPIOB7	GPIOB7	ANB7&ANC15&CMPB_IN2			
27	22	18	GPIOC5	GPIOC5	DACO	XB_IN7		
28	23	19	GPIOB6	GPIOB6	ANB6&ANC14&CMPB_IN1			
29	24	20	GPIOB5	GPIOB5	ANB5&ANC13&CMPC_IN2			
30	25	21	GPIOB4	GPIOB4	ANB4&ANC12&CMPC_IN1			
31	26	22	VDDA	VDDA				
32	27	23	VSSA	VSSA				
33	28	24	GPIOB0	GPIOB0	ANB0&CMPB_IN3			
34	29	25	GPIOB1	GPIOB1	ANB1&CMPB_IN0			
35	30	26	VCAP	VCAP				
36	31	27	GPIOB2	GPIOB2	ANB2&VREFHB&CMPC_IN3			
37	32	—	GPIOA11	GPIOA11	ANC19&VREFHC			
38	33	—	GPIOB8	GPIOB8	ANC20&VREFLC			
39	—	—	GPIOB9	GPIOB9	ANC21	XB_IN9	MISO2	
40	—	—	GPIOB10	GPIOB10	ANC22	XB_IN8	MOSI2	
41	—	—	GPIOB11	GPIOB11	ANC23	XB_IN7	SCLK2	
42	34	28	GPIOB3	GPIOB3	ANB3&VREFLB&CMPC_IN0			
43	35	29	VDD	VDD				
44	36	30	VSS	VSS				
45	—	—	GPIOF11	GPIOF11	TXD0	XB_IN11		
46	—	—	GPIOF15	GPIOF15	RXD0	XB_IN10		
47	37	—	GPIOD7	GPIOD7	XB_OUT11	XB_IN7	MISO1	
48	38	—	GPIOG11	GPIOG11	TB3	CLKO0	MOSI1	
49	39	31	GPIOC6	GPIOC6	TA2	XB_IN3	CMP_REF	
50	40	32	GPIOC7	GPIOC7	SS0_B	TXD0		
51	—	—	GPIOG10	GPIOG10	PWMB_2X	PWMA_2X	XB_IN8	SS2_B
52	41	33	GPIOC8	GPIOC8	MISO0	RXD0	XB_IN9	
53	42	34	GPIOC9	GPIOC9	SCLK0	XB_IN4		
54	43	35	GPIOC10	GPIOC10	MOSI0	XB_IN5	MISO0	
55	44	36	GPIOF0	GPIOF0	XB_IN6	TB2	SCLK1	
56	45	—	GPIOF10	GPIOF10	TXD2	PWMA_FAULT6	PWMB_FAULT6	XB_OUT10
57	46	—	GPIOF9	GPIOF9	RXD2	PWMA_FAULT7	PWMB_FAULT7	XB_OUT11
58	47	37	GPIOC11	GPIOC11	CANTX	SCL1	TXD1	
59	48	38	GPIOC12	GPIOC12	CANRX	SDA1	RXD1	
60	49	39	GPIOF2	GPIOF2	SCL1	XB_OUT6		
61	50	40	GPIOF3	GPIOF3	SDA1	XB_OUT7		
62	51	41	GPIOF4	GPIOF4	TXD1	XB_OUT8		
63	52	42	GPIOF5	GPIOF5	RXD1	XB_OUT9		

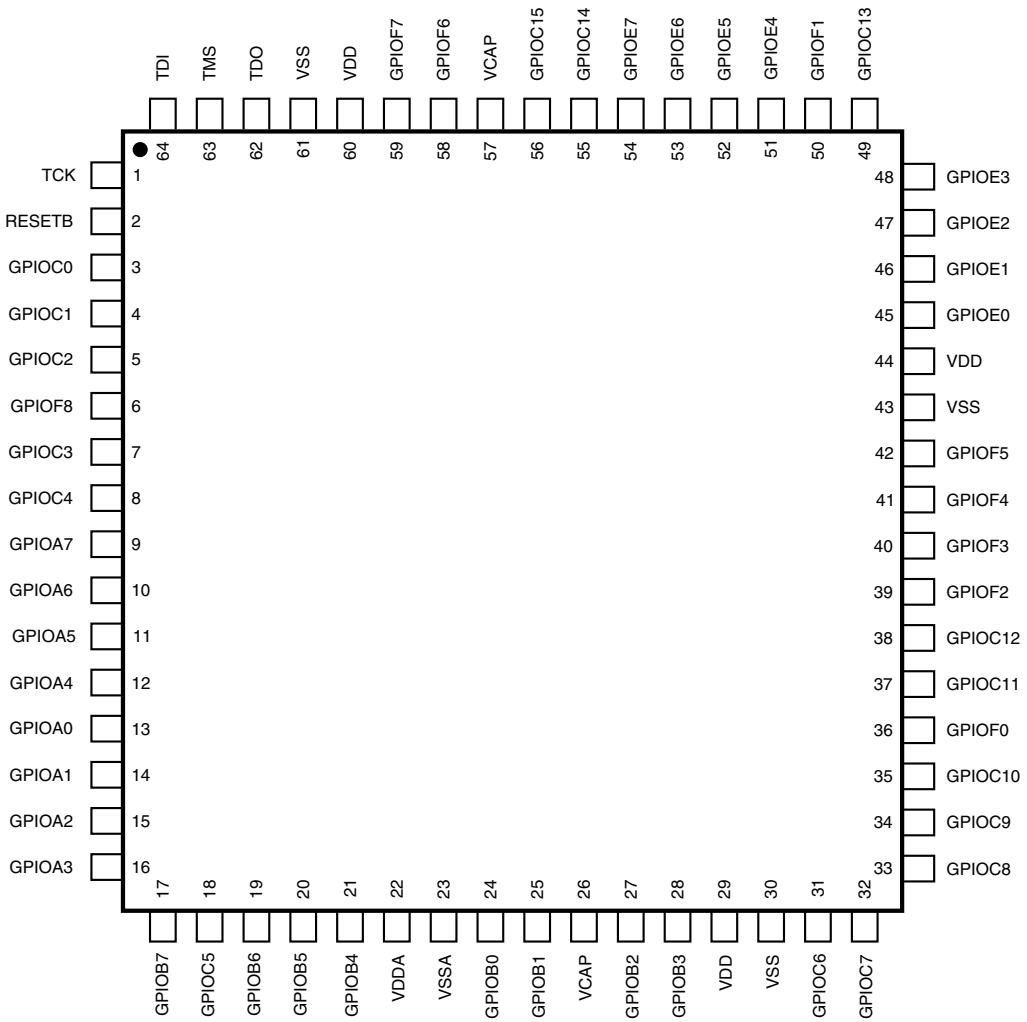

Figure 25. 64-pin LQFP

NOTE

The RESETB pin is a 3.3 V pin only.

Table 37. Revision History

Rev.	Date	Substantial Changes
3	08/2012	In various locations: Clarified that the RESETB pin is a 3.3 V pin only
		MC56F844x/5x/7x Product Family: Clarified that DAC table row applies to 12-bit DAC
		Voltage and current operating ratings: Added rows for RESET input voltage range and RESET output voltage range
		Voltage and current operating requirements: Added row for RESET voltage high, and added new final footnote
		Voltage and current operating behaviors: For Digital Input Current High, created separate sub-rows for Pin Groups 1 and 2
		Power mode transition operating behaviors: Updated row for RESET deassertion to First Address Fetch
		Power consumption operating behaviors: Replaced all TBD values, and updated Typical at 3.3 V I_{DDA} value for WAIT mode
		EMC radiated emissions operating behaviors: Removed this section
		Thermal attributes: Updated values for 100 LQFP
		JTAG Timing: Changed divider value of Max for TCK frequency of operation
		Relaxation Oscillator Timing: Replaced all TBDs, and removed Standby Mode specification for 8 MHz Frequency Variation
		Peripheral operating requirements and behaviors: Updated Flash timing specifications and added Flash high voltage current behaviors
		16-bit ADC electrical characteristics: Updated DNL information about Max value for 16-bit modes and 12-bit modes, and updated INL information about Max value for 16-bit modes
		Signal Multiplexing and Pin Assignments: Added note about GPIOC1, added JTAG signals to table and diagrams, and changed "SCK" signal names to "SCLK"